# **Digital Transistors (BRT)** $R1 = 1 k\Omega$ , $R2 = 1 k\Omega$

### **PNP Transistors with Monolithic Bias Resistor Network**

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a baseemitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

| Rating                         | Symbol               | Max | Unit |
|--------------------------------|----------------------|-----|------|
| Collector-Base Voltage         | $V_{CBO}$            | 50  | Vdc  |
| Collector-Emitter Voltage      | $V_{CEO}$            | 50  | Vdc  |
| Collector Current – Continuous | I <sub>C</sub>       | 100 | mAdc |
| Input Forward Voltage          | V <sub>IN(fwd)</sub> | 10  | Vdc  |
| Input Reverse Voltage          | V <sub>IN(rev)</sub> | 10  | Vdc  |

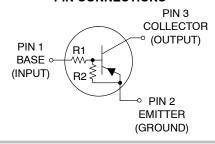
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



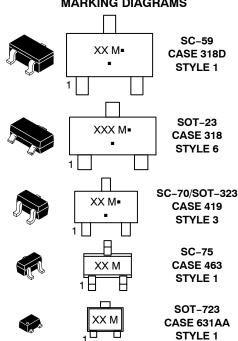
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#### PIN CONNECTIONS



#### **MARKING DIAGRAMS**



XXX = Specific Device Code Μ = Date Code\* = Pb-Free Package

IX ML<sub>1</sub>

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

SOT-1123

CASE 524AA STYLE 1

**Table 1. ORDERING INFORMATION** 

| Device                         | Part Marking | Package                    | Shipping <sup>†</sup> |
|--------------------------------|--------------|----------------------------|-----------------------|
| MUN2130T1G                     | 6G           | SC-59<br>(Pb-Free)         | 3000 / Tape & Reel    |
| MMUN2130LT1G                   | A6G          | SOT-23<br>(Pb-Free)        | 3000 / Tape & Reel    |
| MUN5130T1G                     | 6G           | SC-70/SOT-323<br>(Pb-Free) | 3000 / Tape & Reel    |
| DTA113EET1G                    | 6G           | SC-75<br>(Pb-Free)         | 3000 / Tape & Reel    |
| DTA113EM3T5G, NSVDTA113EM3T5G* | 7E           | SOT-723<br>(Pb-Free)       | 8000 / Tape & Reel    |
| NSBA113EF3T5G                  | L (180°)**   | SOT-1123<br>(Pb-Free)      | 8000 / Tape & Reel    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*\*</sup>  $(xx^\circ)$  = Degree rotation in the clockwise direction.

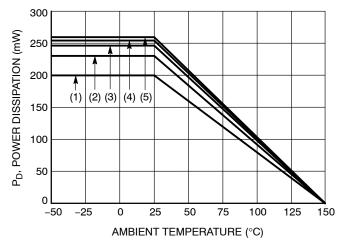


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

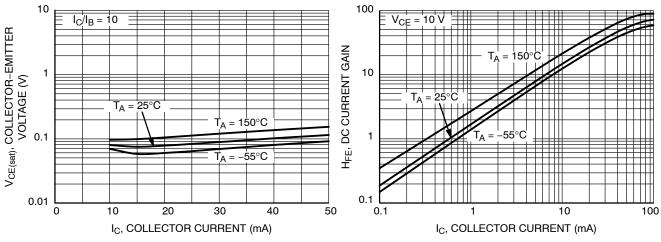


Figure 2. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 3. DC Current Gain

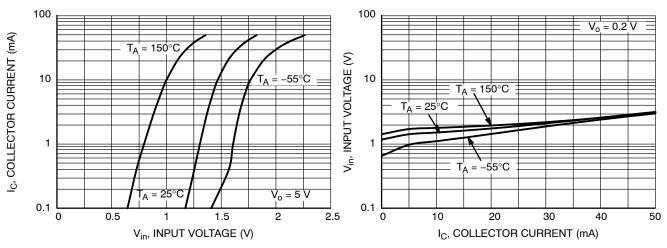


Figure 4. Output Current vs. Input Voltage

Figure 5. Input Voltage vs. Output Current

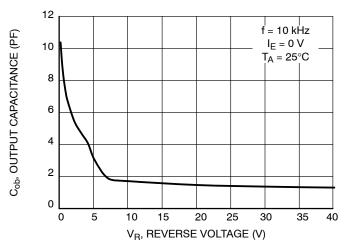


Figure 6. Output Capacitance

**Table 2. THERMAL CHARACTERISTICS** 

| Characteristic   |  | Symbol                            | Max                      | Unit        |
|--|--|-----------------------------------|--------------------------|-------------|
| THERMAL CHARACTERISTICS (SC-59) (MUN2130)                      |  |                                   | •                        |             |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C | (Note 1)<br>(Note 2)<br>(Note 1)<br>(Note 2) | P <sub>D</sub>                    | 230<br>338<br>1.8<br>2.7 | mW<br>mW/°C |
| Thermal Resistance, Junction to Ambient                        | (Note 1)<br>(Note 2)                         | $R_{	heta JA}$                    | 540<br>370               | °C/W        |
| Thermal Resistance,<br>Junction to Lead                        | (Note 1)<br>(Note 2)                         | $R_{	hetaJL}$                     | 264<br>287               | °C/W        |
| Junction and Storage Temperature Range                         |  | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150              | °C          |
| THERMAL CHARACTERISTICS (SOT-23) (MMUN2130L)                   |  |                                   |                          |             |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C | (Note 1)<br>(Note 2)<br>(Note 1)<br>(Note 2) | P <sub>D</sub>                    | 246<br>400<br>2.0<br>3.2 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient                     | (Note 1)<br>(Note 2)                         | $R_{	hetaJA}$                     | 508<br>311               | °C/W        |
| Thermal Resistance,<br>Junction to Lead                        | (Note 1)<br>(Note 2)                         | $R_{	hetaJL}$                     | 174<br>208               | °C/W        |
| Junction and Storage Temperature Range                         |  | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150              | °C          |
| THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5130)              |  |                                   |                          |             |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C | (Note 1)<br>(Note 2)<br>(Note 1)<br>(Note 2) | P <sub>D</sub>                    | 202<br>310<br>1.6<br>2.5 | mW<br>mW/°C |
| Thermal Resistance, Junction to Ambient                        | (Note 1)<br>(Note 2)                         | $R_{	hetaJA}$                     | 618<br>403               | °C/W        |
| Thermal Resistance,<br>Junction to Lead                        | (Note 1)<br>(Note 2)                         | $R_{	hetaJL}$                     | 280<br>332               | °C/W        |
| Junction and Storage Temperature Range                         |  | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150              | °C          |
| THERMAL CHARACTERISTICS (SC-75) (DTA113EE)                     |  |                                   |                          |             |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C | (Note 1)<br>(Note 2)<br>(Note 1)<br>(Note 2) | P <sub>D</sub>                    | 200<br>300<br>1.6<br>2.4 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient                     | (Note 1)<br>(Note 2)                         | $R_{	hetaJA}$                     | 600<br>400               | °C/W        |
| Junction and Storage Temperature Range                         | _  | $T_J,T_stg$                       | -55 to +150              | °C          |
| THERMAL CHARACTERISTICS (SOT-723) (DTA113EM3)                  |  |                                   |                          |             |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C | (Note 1)<br>(Note 2)<br>(Note 1)<br>(Note 2) | P <sub>D</sub>                    | 260<br>600<br>2.0<br>4.8 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient                     | (Note 1)<br>(Note 2)                         | $R_{	hetaJA}$                     | 480<br>205               | °C/W        |
| Junction and Storage Temperature Range                         |  | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150              | °C          |

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 lnch Pad.
  3. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
  4. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 2. THERMAL CHARACTERISTICS** 

| Characteristic  |  | Symbol                            | Max                      | Unit        |
|---|--|-----------------------------------|--------------------------|-------------|
| THERMAL CHARACTERISTICS (SOT-1123) (NSBA113EF3)                         |  |                                   |                          |             |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$ | (Note 3)<br>(Note 4)<br>(Note 3)<br>(Note 4) | P <sub>D</sub>                    | 254<br>297<br>2.0<br>2.4 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient                              | (Note 3)<br>(Note 4)                         | $R_{	hetaJA}$                     | 493<br>421               | °C/W        |
| Thermal Resistance, Junction to Lead                                    | (Note 3)                                     | $R_{	hetaJL}$                     | 193                      | °C/W        |
| Junction and Storage Temperature Range                                  |  | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150              | °C          |

<sup>1.</sup> FR-4 @ Minimum Pad.

Table 3. ELECTRICAL CHARACTERISTICS ( $T_A = 25$ °C, unless otherwise noted)

| Characteristic   | Symbol                | Min | Тур | Max  | Unit |
|--|-----------------------|-----|-----|------|------|
| OFF CHARACTERISTICS  |                       | •   | •   |      |      |
| Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$   | I <sub>CBO</sub>      | _   | -   | 100  | nAdc |
| Collector-Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)                            | I <sub>CEO</sub>      | _   | -   | 500  | nAdc |
| Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)                                | I <sub>EBO</sub>      | _   | -   | 4.3  | mAdc |
| Collector–Base Breakdown Voltage ( $I_C = 10 \mu A, I_E = 0$ )   | V <sub>(BR)</sub> CBO | 50  | -   | -    | Vdc  |
| Collector-Emitter Breakdown Voltage (Note 5) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)               | V <sub>(BR)</sub> CEO | 50  | -   | -    | Vdc  |
| ON CHARACTERISTICS   |                       | •   | •   |      |      |
| DC Current Gain (Note 5)<br>(I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)                            | h <sub>FE</sub>       | 3.0 | 5.0 | -    |      |
| Collector-Emitter Saturation Voltage (Note 5) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 5.0 mA)          | V <sub>CE(sat)</sub>  | _   | -   | 0.25 | Vdc  |
| Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A})$                                    | V <sub>i(off)</sub>   | _   | 1.2 | 0.5  | Vdc  |
| Input Voltage (on)<br>(V <sub>CE</sub> = 0.3 V, I <sub>C</sub> = 20 mA)                                  | V <sub>i(on)</sub>    | 2.0 | 1.6 | -    | Vdc  |
| Output Voltage (on) ( $V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )         | V <sub>OL</sub>       | _   | -   | 0.2  | Vdc  |
| Output Voltage (off) ( $V_{CC} = 5.0 \text{ V}$ , $V_B = 0.05 \text{ V}$ , $R_L = 1.0 \text{ k}\Omega$ ) | V <sub>OH</sub>       | 4.9 | -   | -    | Vdc  |
| Input Resistor   | R1                    | 0.7 | 1.0 | 1.3  | kΩ   |
| Resistor Ratio   | $R_1/R_2$             | 0.8 | 1.0 | 1.2  |      |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

FR-4 @ 1.0 x 1.0 Inch Pad.
 FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
 FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.





**SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

|     | MILLIM | MILLIMETERS |      |       | INCHES |       |  |
|-----|--------|-------------|------|-------|--------|-------|--|
| DIM | MIN.   | N□M.        | MAX. | MIN.  | N□M.   | MAX.  |  |
| Α   | 0.89   | 1.00        | 1.11 | 0.035 | 0.039  | 0.044 |  |
| A1  | 0.01   | 0.06        | 0.10 | 0.000 | 0.002  | 0.004 |  |
| b   | 0.37   | 0.44        | 0.50 | 0.015 | 0.017  | 0.020 |  |
| С   | 0.08   | 0.14        | 0.20 | 0.003 | 0.006  | 0.008 |  |
| D   | 2.80   | 2.90        | 3.04 | 0.110 | 0.114  | 0.120 |  |
| Ε   | 1.20   | 1.30        | 1.40 | 0.047 | 0.051  | 0.055 |  |
| e   | 1.78   | 1.90        | 2.04 | 0.070 | 0.075  | 0.080 |  |
| L   | 0.30   | 0.43        | 0.55 | 0.012 | 0.017  | 0.022 |  |
| L1  | 0.35   | 0.54        | 0.69 | 0.014 | 0.021  | 0.027 |  |
| HE  | 2.10   | 2.40        | 2.64 | 0.083 | 0.094  | 0.104 |  |
| Т   | 0*     |             | 10°  | 0*    |        | 10°   |  |

# GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **STYLES ON PAGE 2**

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| DESCRIPTION:     | SOT-23 (TO-236) |  | PAGE 1 OF 2 |  |

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



#### **SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

| STYLE 1 THRU 5:<br>CANCELLED                            | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE           | N   |   |
|---|---|---|---|---|---|
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE      | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE     | STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE          | STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE                | STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE             | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          |
| STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE      | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE | STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>N PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE          |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN       | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT   | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE           | STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE            | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION |
| STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE     |   |   |   |   |

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|------------------|-----------------|--|-------------|--|
| DESCRIPTION:     | SOT-23 (TO-236) |  | PAGE 2 OF 2 |  |

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SC-70 (SOT-323) **CASE 419** ISSUE R

END VIEW

**DATE 11 OCT 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

|     | M:       | MILLIMETERS |      |           | INCHES   |       |
|-----|----------|-------------|------|-----------|----------|-------|
| DIM | MIN.     | N□M.        | MAX. | MIN.      | N□M.     | MAX.  |
| Α   | 0.80     | 0.90        | 1.00 | 0.032     | 0.035    | 0.040 |
| A1  | 0.00     | 0.05        | 0.10 | 0.000     | 0.002    | 0.004 |
| A2  |          | 0.70 REF    | -    | 0.028 BSC |          |       |
| b   | 0.30     | 0.35        | 0.40 | 0.012     | 0.014    | 0.016 |
| С   | 0.10     | 0.18        | 0.25 | 0.004     | 0.007    | 0.010 |
| D   | 1.80     | 2.00        | 2.20 | 0.071     | 0.080    | 0.087 |
| E   | 1.15     | 1.24        | 1.35 | 0.045     | 0.049    | 0.053 |
| е   | 1.20     | 1.30        | 1.40 | 0.047     | 0.051    | 0.055 |
| e1  | 0.65 BSC |             |      |           | 0.026 BS | C     |
| L   | 0.20     | 0.38        | 0.56 | 0.008     | 0.015    | 0.022 |
| HE  | 2.00     | 2.10        | 2.40 | 0.079     | 0.083    | 0.095 |



#### **GENERIC MARKING DIAGRAM**

SIDE VIEW



= Specific Device Code XX

М = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

| STYLE 1:<br>CANCELLED       | STYLE 2:<br>PIN 1. ANODE<br>2. N.C.<br>3. CATHODE | STYLE 3:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE | STYLE 5:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE |                           |
|-----------------------------|---|---|--|--|---------------------------|
| STYLE 6:                    | STYLE 7:  | STYLE 8:  | STYLE 9:   | STYLE 10:  | STYLE 11:                 |
| PIN 1. EMITTER              | PIN 1. BASE                                       | PIN 1. GATE   | PIN 1. ANODE   | PIN 1. CATHODE                                     | PIN 1. CATHODE            |
| 2. BASE                     | 2. EMITTER  | 2. SOURCE   | 2. CATHODE   | 2. ANODE   | <ol><li>CATHODE</li></ol> |
| <ol><li>COLLECTOR</li></ol> | <ol><li>COLLECTOR</li></ol>                       | 3. DRAIN  | <ol><li>CATHODE-ANODE</li></ol>                      | 3. ANODE-CATHODE                                   | <ol><li>CATHODE</li></ol> |

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|------------------|-----------------|---|-------------|--|
| DESCRIPTION:     | SC-70 (SOT-323) |   | PAGE 1 OF 1 |  |

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#### SC75-3 1.60x0.80x0.80, 1.00P **CASE 463 ISSUE H**

**DATE 01 FEB 2024** 

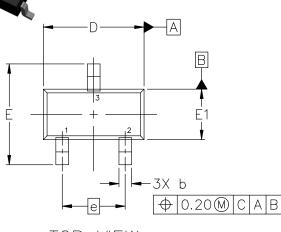
#### NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

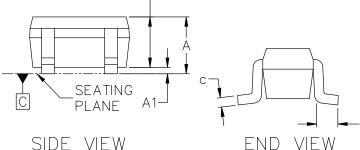
| DIM | MILLIMETERS |      |      |  |
|-----|-------------|------|------|--|
|     | MIN.        | NOM. | MAX. |  |
| А   | 0.70        | 0.80 | 0.90 |  |
| A1  | 0.00        | 0.05 | 0.10 |  |
| A2  | 0.80 REF.   |      |      |  |
| b   | 0.15        | 0.20 | 0.30 |  |
| С   | 0.10        | 0.15 | 0.25 |  |
| D   | 1.55        | 1.60 | 1.65 |  |
| E   | 1.50        | 1.60 | 1.70 |  |
| E1  | 0.70        | 0.80 | 0.90 |  |
| е   | 1.00 BSC    |      |      |  |
| L   | 0.10        | 0.15 | 0.20 |  |

0.356

0.787



VIEW



A2

SIDE VIEW

#### **GENERIC MARKING DIAGRAM\***



XX= Specific Device Code

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. EMITTER

PIN 1. CATHODE 2. CATHODE

3. ANODE

STYLE 4:

STYLE 2: PIN 1. ANODE 2. N/C 3. COLLECTOR 3. CATHODE

STYLE 5:

PIN 1. GATE 2. SOURCE

3. DRAIN

STYLE 3: PIN 1. ANODE 2. ANODE

3. CATHODE

1.000 RECOMMENDED MOUNTING FOOTPRINT\*

1.803

0.508

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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| DESCRIPTION:     | SC75-3 1.60x0.80x0.80, 1.00P   |  | PAGE 1 OF 1 |

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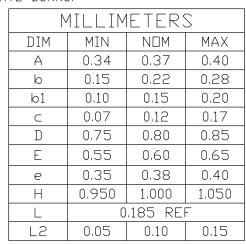


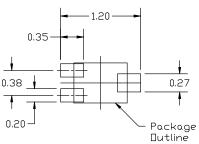
#### SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

**DATE 18 JAN 2024** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
  OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



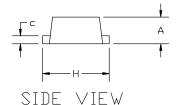


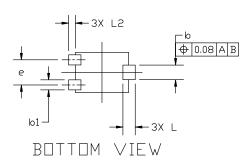
# RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download th e □N Semiconductor Soldering and Mounting Techniques Reference manual, S□L□ERRM/□.

| - I | B<br>I |
|-----|--------|
|     | E<br>U |

THP VIFW





# GENERIC MARKING DIAGRAM\*



X = Specific Device Code

M = Date Code

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| YLE 1:                      | STYLE 2:                  | STYLE 3:                  | STYLE 4:       | STYLE 5:                 |
|-----------------------------|---------------------------|---------------------------|----------------|--------------------------|
| PIN 1. BASE                 | PIN 1. ANODE              | PIN 1. ANODE              | PIN 1. CATHODE | PIN 1. GATE              |
| <ol><li>EMITTER</li></ol>   | 2. N/C                    | 2. ANODE                  | 2. CATHODE     | <ol><li>SOURCE</li></ol> |
| <ol><li>COLLECTOR</li></ol> | <ol><li>CATHODE</li></ol> | <ol><li>CATHODE</li></ol> | 3. ANODE       | 3. DRAIN                 |

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| DESCRIPTION:     | SOT-1123 0.80x0.60x0.37, | SOT-1123 0.80x0.60x0.37, 0.35P   |  |  |

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MILLIMETERS

 $N\square M$ .

0.50



#### SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

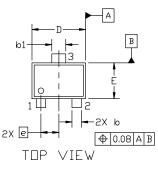
**DATE 24 JAN 2024** 

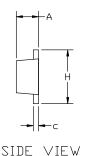
MAX.

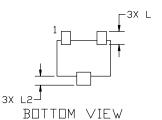
0.55

#### NOTES:

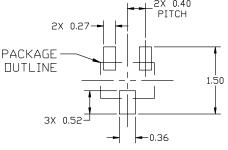
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.







| b    | 0.15     | 0.21     | 0.27 |
|------|----------|----------|------|
| b1   | 0.25     | 0.31     | 0.37 |
| С    | 0.07     | 0.12     | 0.17 |
| D    | 1.15     | 1.20     | 1.25 |
| Е    | 0.75     | 0.80     | 0.85 |
| е    | 0.40 BSC |          |      |
| Н    | 1.15     | 1.20     | 1.25 |
| L    |          | 0.29 REF | -    |
| L2   | 0.15     | 0.20     | 0.25 |
| 0.27 |          |          |      |



DIM

Α

MIN.

0.45

#### RECOMMENDED MOUNTING FUUTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

| STYLE 1:                    | STYLE 2:                  | STYLE 3:                  | STYLE 4:                | STYLE 5:                 |
|-----------------------------|---------------------------|---------------------------|-------------------------|--------------------------|
| PIN 1. BASE                 | PIN 1. ANODE              | PIN 1. ANODE              | PIN 1. CATHODE          | PIN 1. GATE              |
| <ol><li>EMITTER</li></ol>   | 2. N/C                    | 2. ANODE                  | 2. CATHODE              | <ol><li>SOURCE</li></ol> |
| <ol><li>COLLECTOR</li></ol> | <ol><li>CATHODE</li></ol> | <ol><li>CATHODE</li></ol> | <ol><li>ANODE</li></ol> | <ol><li>DRAIN</li></ol>  |

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